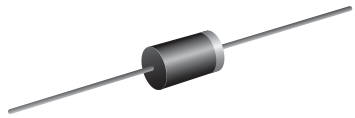
2FWJ42M

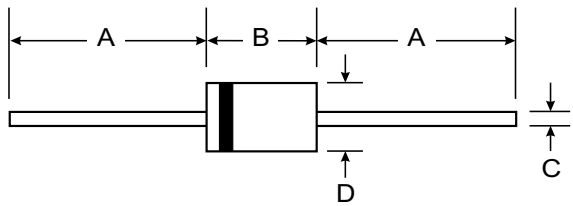
SCHOTTKY BARRIER RECTIFIER DIODES

VOLTAGE RANGE: 30V
CURRENT: 2.0 A



Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



DO-15		
Dim	**Min**	**Max**
A	25.40	—
B	5.50	7.62
C	0.686	0.889
D	2.60	3.60
All Dimensions in mm		

Mechanical Data

- Case: DO-15, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.40 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

RoHS COMPLIANT

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	2FWJ42M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	30	V
RMS Reverse Voltage	$V_{R(RMS)}$	21	V
Average Rectified Output Current @T_L = 100°C (Note 1)	I_O	2.0	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	50	A
Forward Voltage @I_F = 2.0A	V_{FM}	0.50	V
Peak Reverse Current @T_A = 25°C At Rated DC Blocking Voltage @T_A = 100°C	I_{RM}	0.5 10	mA
Typical Junction Capacitance (Note 2)	C_j	170	pF
Typical Thermal Resistance (Note 1)	$R_{\theta JA}$	35	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	°C

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.
2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.